

# 300mW, NPN Small Signal Transistor

#### **FEATURES**

- Epitaxial planar die construction
- Surface device type mounting
- Moisture sensitivity level 1
- Matte Tin (Sn) lead finish with Nickel (Ni) underplate
- Pb free version and RoHS compliant
- Packing code with suffix "G" means green compound (halogen-free)

### **MECHANICAL DATA**

- Case: SOT- 23, molded plastic
- Terminal: Matte tin plated, lead free,
- solderable per MIL-STD-202, Method 208 guaranteed
- High temperature soldering guaranteed: 260°C/10s
- Weight: 0.008g (approximately)
- Marking Code: 1AM















MAXIMUM RATINGS AND ELECTRICAL CHARACTERSTICS (T <sub>A</sub> =25°C unless otherwise noted)				
PARAMETER	SYMBOL	VALUE	UNIT	
Power Dissipation	P <sub>D</sub>	300	mW	
Collector-Base Voltage	V <sub>CBO</sub>	60	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V	
Emitter-Base Voltage	V <sub>EBO</sub>	6	V	
Collector Current	I <sub>C</sub>	200	mA	
Junction and Storage Temperature Range	$T_J,T_STG$	-55 to +150	°C	

Notes:1. Valid provided that electrodes are kept at ambient temperature

PARAMETER				SYMBOL	MIN	MAX	UNIT
Collector-Base Breakdov	wn Voltage	I <sub>C</sub> = 10 μA	I <sub>E</sub> = 0	$V_{(BR)CBO}$	60	-	V
Collector-Emitter Breakd	lown Voltage	I <sub>C</sub> = 1 mA	I <sub>B</sub> = 0	$V_{(BR)CEO}$	40	-	V
Emitter-Base Breakdowr	n Voltage	I <sub>E</sub> = 10 μA	I <sub>C</sub> = 0	$V_{(BR)EBO}$	6	-	V
Collector Cut-off Current		V <sub>CB</sub> = 60 V	I <sub>E</sub> = 0	I <sub>CBO</sub>	-	0.1	μA
Collector Cut-off Current		V <sub>CE</sub> = 30 V	V <sub>BE(OFF)</sub> = 3 V	I <sub>CEO</sub>	-	50	nA
Emitter Cut-off Current		V <sub>EB</sub> = 5 V	I <sub>C</sub> = 0	I <sub>EBO</sub>	-	0.1	μA
		V <sub>CE</sub> = 1 V	I <sub>C</sub> = 10 mA		100	400	
DC Current Gain		$V_{CE} = 1 V$	$I_C = 50 \text{ mA}$	h <sub>FE</sub>	60	-	
		$V_{CE} = 1 V$	$I_{\rm C}$ = 100 mA		30	-	
Collector-Emitter Saturat	tion Voltage	$I_C = 50 \text{ mA}$	I <sub>B</sub> = 5 mA	V <sub>CE(sat)</sub>	-	0.3	V
Base-Emitter Saturation	Voltage	$I_C = 50 \text{ mA}$	I <sub>B</sub> = 5 mA	$V_{BE(sat)}$	-	0.95	V
Transition frequency	V <sub>CE</sub> = 20 V	$I_C = 10 \text{ mA}$	f= 100MHz	f <sub>T</sub>	250	-	MHz
Delay time	V <sub>CC</sub> = 3 V	V <sub>BE</sub> = 0.5 V	I <sub>C</sub> = 10 mA	t <sub>d</sub>	-	35	ns
Rise time			$I_{B1} = 1.0 \text{ mA}$	t <sub>r</sub>	-	35	ns
Storage time		V <sub>CC</sub> = 3 V	I <sub>C</sub> = 10 mA	t <sub>s</sub>	-	200	ns
Fall time		$I_{B1} = I_{B2} = 1.0$	mA	t <sub>f</sub>	-	50	ns

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#### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub>=25°C unless otherwise noted)

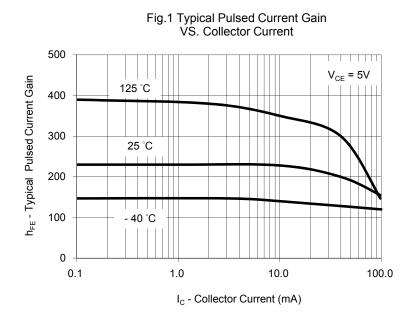


Fig. 2 Collector-Emitter Saturation Voltage VS. Collector Current

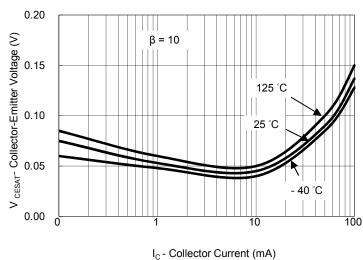


Fig. 3 Base-Emitter Saturation Voltage VS. Collector Current

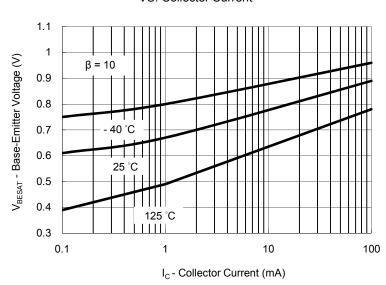


Fig. 4 Base-Emitter On Voltage VS. Collector Current

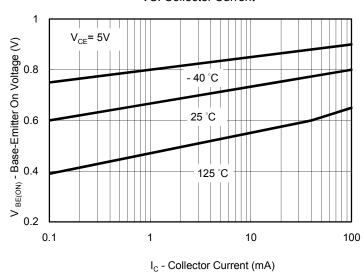


Fig. 5 Collector-Cutoff Current VS. Ambient Temperature

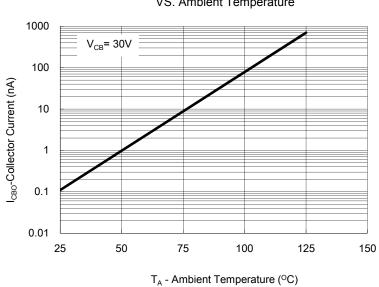
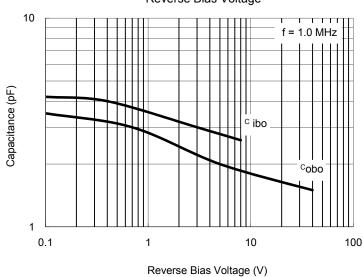


Fig. 6 Capacitance VS. Reverse Bias Voltage



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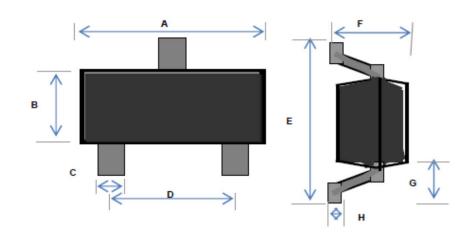


ORDERING	ORDERING INFORMATION				
PART NO.	PART NO. SUFFIX (Note 1)	PACKING CODE	PACKING CODE SUFFIX	PACKAGE	PACKING
MMBT3904	-XX	RF	G	SOT-23	3K / 7" Reel
WIND 1 3904	-88	R5	9	301-23	10K / 13" Reel

Note 1: Part No. Suffix "-xx " would be used for special requirement

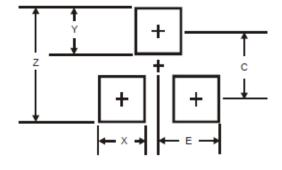
EXAMPLE					
PREFERRED P/N	PART NO.	PART NO. SUFFIX	PACKING CODE	PACKING CODE SUFFIX	DESCRIPTION
MMBT3904 RF	MMBT3904		RF		Multiple manufacture source
MMBT3904 RFG	MMBT3904		RF	G	Multiple manufacture source Green compound
MMBT3904-D0 RFG	MMBT3904	-D0	RF	G	Defined manufacture source Green compound
MMBT3904-B0 RFG	MMBT3904	-B0	RF	G	Defined manufacture source Green compound

### PACKAGE OUTLINE DIMENSIONS



DIM.	Unit(mm)		Unit(inch)	
DIIVI.	Min	Max	Min	Max
Α	2.70	3.10	0.106	0.122
В	1.10	1.50	0.043	0.059
С	0.30	0.51	0.012	0.020
D	1.78	2.04	0.070	0.080
E	2.10	2.64	0.083	0.104
F	0.89	1.30	0.035	0.051
G	0.55 REF		0.022	REF
Н	0.10 REF		0.004	REF

## **SUGGEST PAD LAYOUT**



DIM	Unit (mm)	Unit (inch)	
DIIVI	TYP	TYP	
Z	2.8	0.11	
Х	0.7	0.03	
Υ	0.9	0.04	
С	1.9	0.07	
Е	1.0	0.04	





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